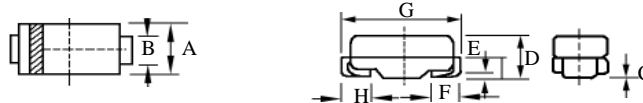


EFM101 – EFM106
1A 片式快速二极管
1A FAST RECOVERY SMA DIODES

型号 TYPE	印字 Marking	反向重复 峰值电压 $V_{RRM}(V)$	正向 平均电流 $I_F(A)$	正向 峰值电压 $V_F(V)$	反向 峰值电流 $I_{RM}(\mu A)$	正向 浪涌电流 $I_{FSM}(A)$	反向 恢复时间 $T_{rr}(ns)$	外形尺寸 Package Dimensions
EFM101	EF1	50	1.0	0.95	5.0	30	35	DO – 214AC
EFM102	EF2	100		0.95				
EFM103	EF3	150		0.95				
EFM104	EF4	200		0.95				
EFM105	EF5	300		1.25				
EFM106	EF6	400		1.25				

Trr 测试条件: $I_F=1A, I_R=0.5A, I_{RR}=0.25A$

Trr Test Conditions: $I_F=1A, I_R=0.5A, I_{RR}=0.25A$



A	B	C	D	E	F	G	H
$\frac{.110(2.8)}{.086(2.2)}$	$\frac{.067(1.7)}{.051(1.3)}$	$\frac{.008}{(.2)} \text{ MAX}$	$\frac{.091(2.3)}{.067(1.7)}$	$\frac{.051(1.3)}{.008(0.2)}$	$\frac{.059(1.5)}{.035(0.9)}$	$\frac{.209(5.3)}{.185(4.7)}$	$\frac{.059(1.5)}{.035(0.9)}$

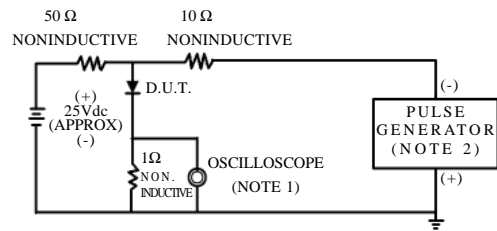
DO – 214AC

EFM101 –EFM106

1 A 片式快速二极管额定值与特性曲线

RATING & CHARACTERISTIC CURVES OF 1A FAST RECOVERY SMA DIODES

FIG.1-TEST CIRCUIT DIAGRAM AND REVERSE RECOVERY TIME CHARACTERISTIC



NOTES:1.Rise Time=7ns max.
Input Impedance=1megohm.22pF.
2.Rise Time=10ns max.
Source Impedance=50 ohms.

FIG. 2 - TYPICAL FORWARD CURRENT DERATING CURVE

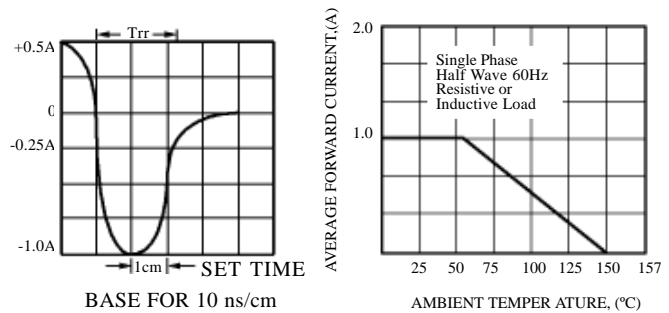


FIG. 3 - TYPICAL REVERSE CHARACTERISTICS

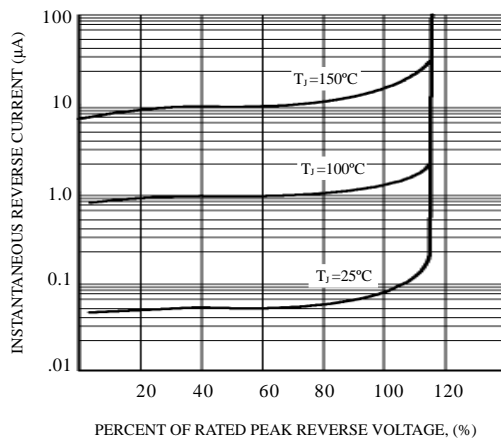


FIG. 4 - TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

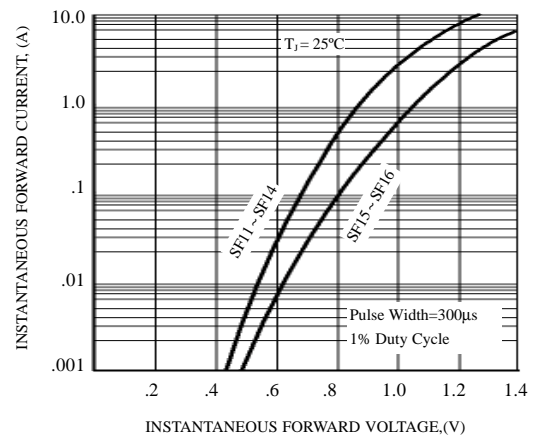


FIG. 5 - MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

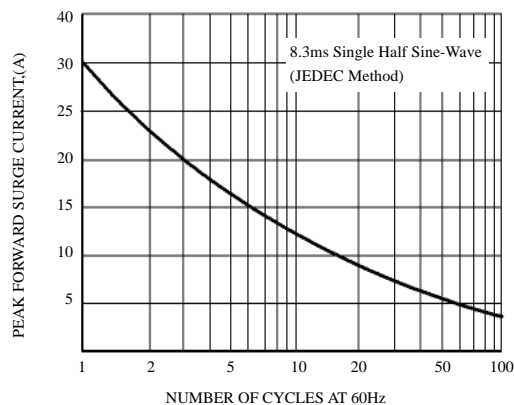


FIG. 6 - TYPICAL JUNCTION CAPACITANCE

